

## NCE N-Channel Super Trench Power MOSFET

### Description

The NCEP0135A uses **Super Trench** technology that is uniquely optimized to provide the most efficient high frequency switching performance. Both conduction and switching power losses are minimized due to an extremely low combination of  $R_{DS(ON)}$  and  $Q_g$ . This device is ideal for high-frequency switching and synchronous rectification.

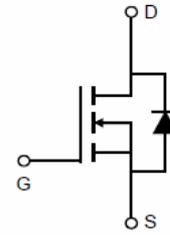
### General Features

- $V_{DS} = 100V, I_D = 35A$   
 $R_{DS(ON)} = 18m\Omega$  (typical) @  $V_{GS} = 10V$   
 $R_{DS(ON)} = 22m\Omega$  (typical) @  $V_{GS} = 4.5V$
- Excellent gate charge x  $R_{DS(on)}$  product(FOM)
- Very low on-resistance  $R_{DS(on)}$
- 150 °C operating temperature
- Pb-free lead plating
- 100% UIS tested

### Application

- DC/DC Converter
- Ideal for high-frequency switching and synchronous rectification

**100% UIS TESTED!**  
**100%  $\Delta V_{ds}$  TESTED!**



Schematic Diagram



Marking and pin assignment



TO-220-3L top view

### Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
NCEP0135A	NCEP0135A	TO-220-3L	-	-	-

### Absolute Maximum Ratings ( $T_C = 25^\circ C$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	$V_{DS}$	100	V
Gate-Source Voltage	$V_{GS}$	$\pm 20$	V
Drain Current-Continuous (Silicon Limited)	$I_D$	35	A
Drain Current-Continuous( $T_C = 100^\circ C$ )	$I_D(100^\circ C)$	24.7	A
Pulsed Drain Current (Package Limited)	$I_{DM}$	180	A
Maximum Power Dissipation	$P_D$	110	W
Derating factor		0.73	W/ $^\circ C$
Single pulse avalanche energy (Note 5)	$E_{AS}$	200	mJ
Operating Junction and Storage Temperature Range	$T_J, T_{STG}$	-55 To 175	$^\circ C$

## Thermal Characteristic

Thermal Resistance, Junction-to-Case <sup>(Note 2)</sup>	$R_{\theta JC}$	1.36	°C/W
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## Electrical Characteristics ( $T_C=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
<b>Off Characteristics</b>						
Drain-Source Breakdown Voltage	$BV_{DSS}$	$V_{GS}=0V, I_D=250\mu A$	100		-	V
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS}=100V, V_{GS}=0V$	-	-	1	$\mu A$
Gate-Body Leakage Current	$I_{GSS}$	$V_{GS}=\pm 20V, V_{DS}=0V$	-	-	$\pm 100$	nA
<b>On Characteristics</b> <sup>(Note 3)</sup>						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	1.2	2.0	2.8	V
Drain-Source On-State Resistance	$R_{DS(on)}$	$V_{GS}=10V, I_D=20A$	-	18	23	m $\Omega$
		$V_{GS}=4.5V, I_D=20A$	-	22	27	m $\Omega$
Forward Transconductance	$g_{FS}$	$V_{DS}=5V, I_D=20A$	-	35	-	S
<b>Dynamic Characteristics</b> <sup>(Note 4)</sup>						
Input Capacitance	$C_{iss}$	$V_{DS}=50V, V_{GS}=0V,$ $F=1.0\text{MHz}$	-	1600	-	PF
Output Capacitance	$C_{oss}$		-	139	-	PF
Reverse Transfer Capacitance	$C_{rss}$		-	11	-	PF
<b>Switching Characteristics</b> <sup>(Note 4)</sup>						
Turn-on Delay Time	$t_{d(on)}$	$V_{DD}=50V, I_D=20A$ $V_{GS}=10V, R_G=1.6\Omega$	-	6	-	nS
Turn-on Rise Time	$t_r$		-	2	-	nS
Turn-Off Delay Time	$t_{d(off)}$		-	18	-	nS
Turn-Off Fall Time	$t_f$		-	2	-	nS
Total Gate Charge	$Q_g$	$V_{DS}=50V, I_D=20A,$ $V_{GS}=10V$	-	26	-	nC
Gate-Source Charge	$Q_{gs}$		-	7.4	-	nC
Gate-Drain Charge	$Q_{gd}$		-	3.8	-	nC
<b>Drain-Source Diode Characteristics</b>						
Diode Forward Voltage <sup>(Note 3)</sup>	$V_{SD}$	$V_{GS}=0V, I_S=35A$	-		1.2	V
Diode Forward Current <sup>(Note 2)</sup>	$I_S$		-	-	35	A
Reverse Recovery Time	$t_{rr}$	$T_J = 25^\circ\text{C}, I_F = 20A$ $di/dt = 500A/\mu s$ <sup>(Note 3)</sup>	-		26	nS
Reverse Recovery Charge	$Q_{rr}$		-		98	nC

### Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board,  $t \leq 10$  sec.
3. Pulse Test: Pulse Width  $\leq 300\mu s$ , Duty Cycle  $\leq 2\%$ .
4. Guaranteed by design, not subject to production
5. EAS condition :  $T_J=25^\circ\text{C}, V_{DD}=20V, V_G=10V, L=0.5\text{mH}, R_g=25\Omega$

Typical Electrical and Thermal Characteristics

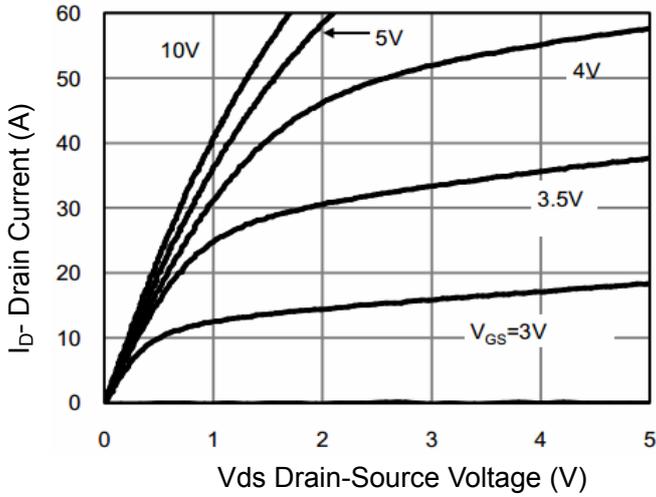


Figure 1 Output Characteristics

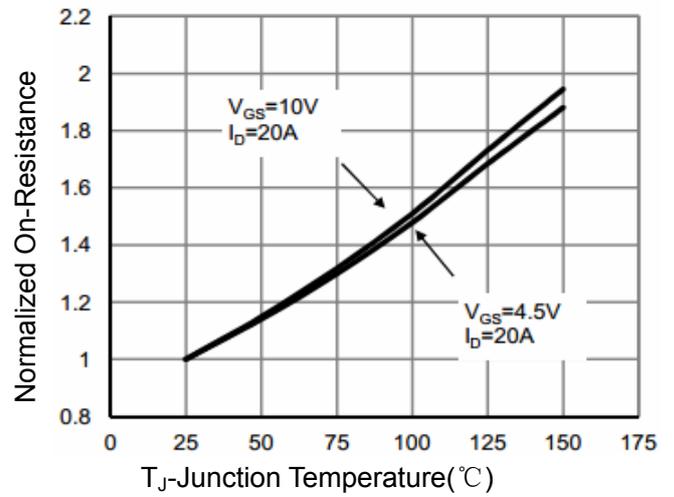


Figure 4  $R_{dson}$ -Junction Temperature

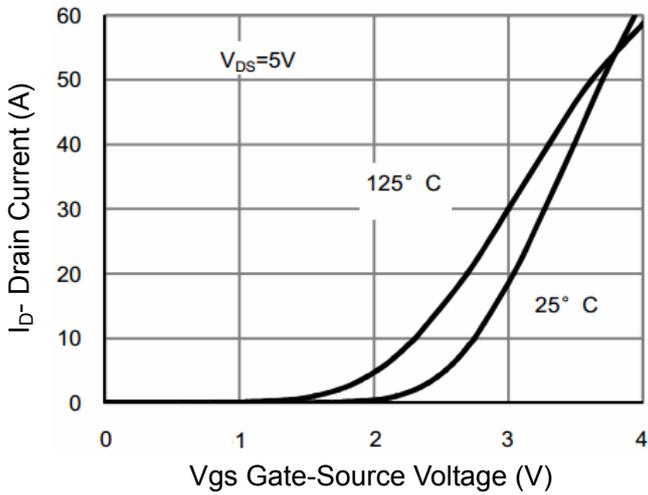


Figure 2 Transfer Characteristics

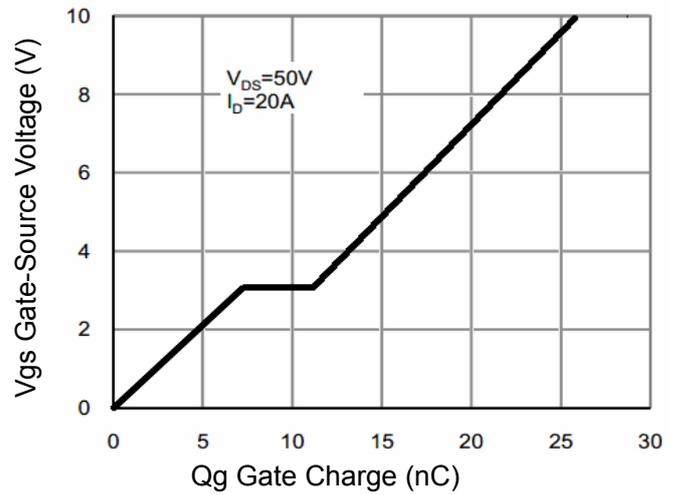


Figure 5 Gate Charge

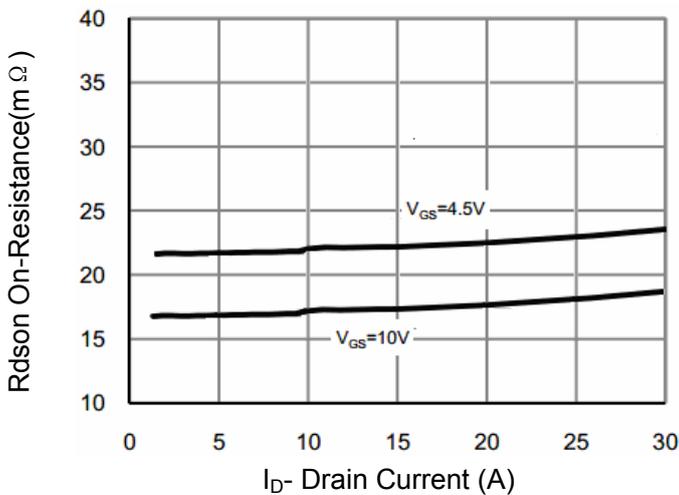


Figure 3  $R_{dson}$ - Drain Current

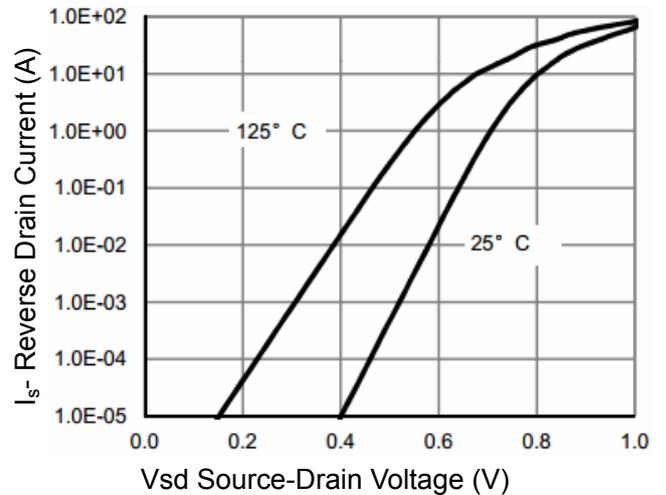
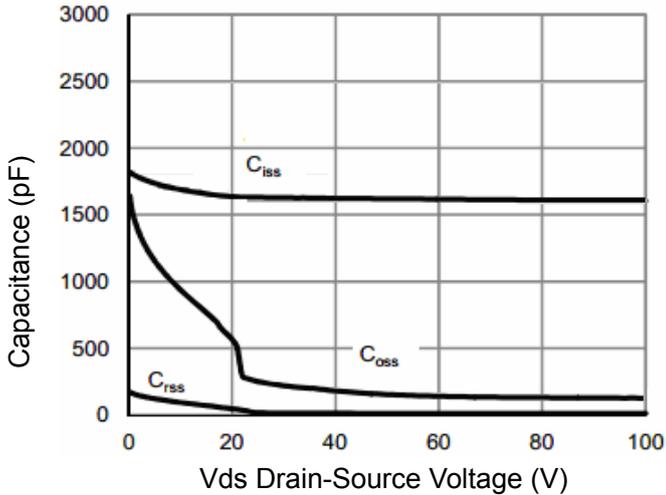
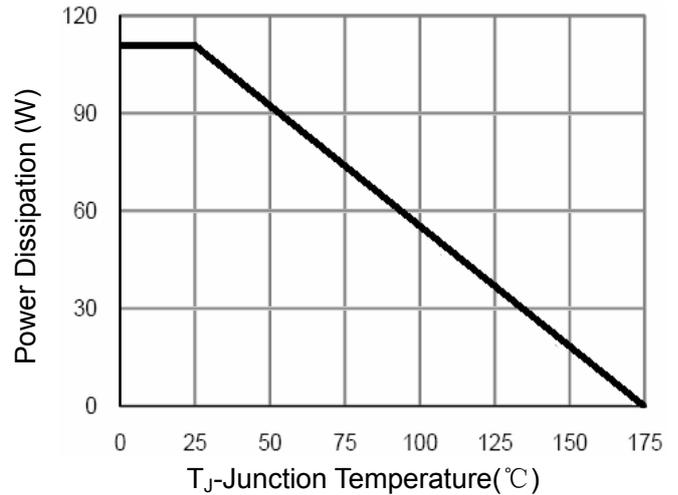


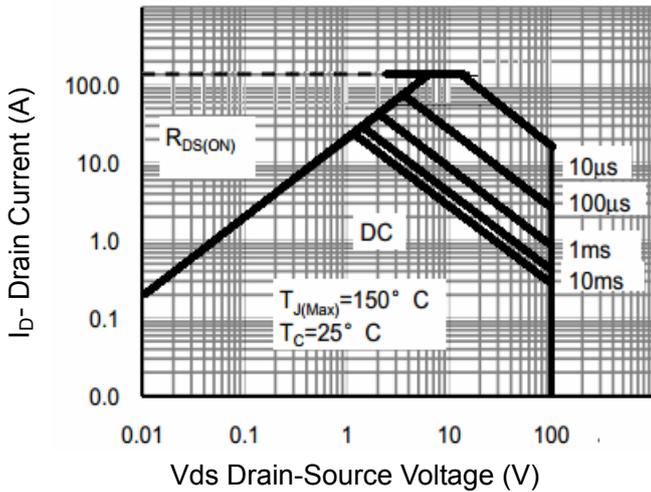
Figure 6 Source- Drain Diode Forward



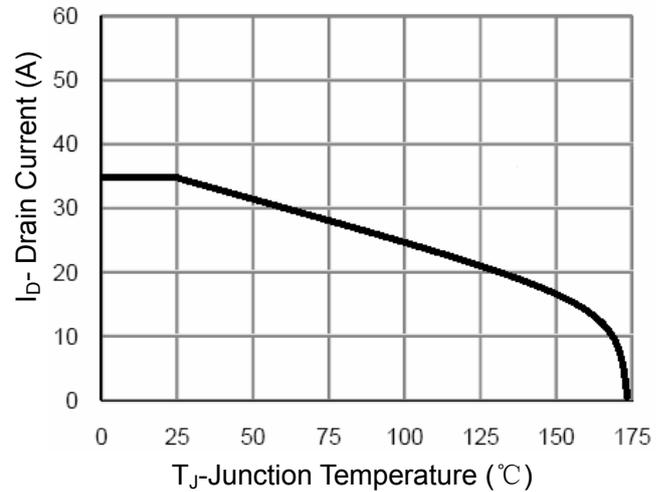
**Figure 7 Capacitance vs Vds**



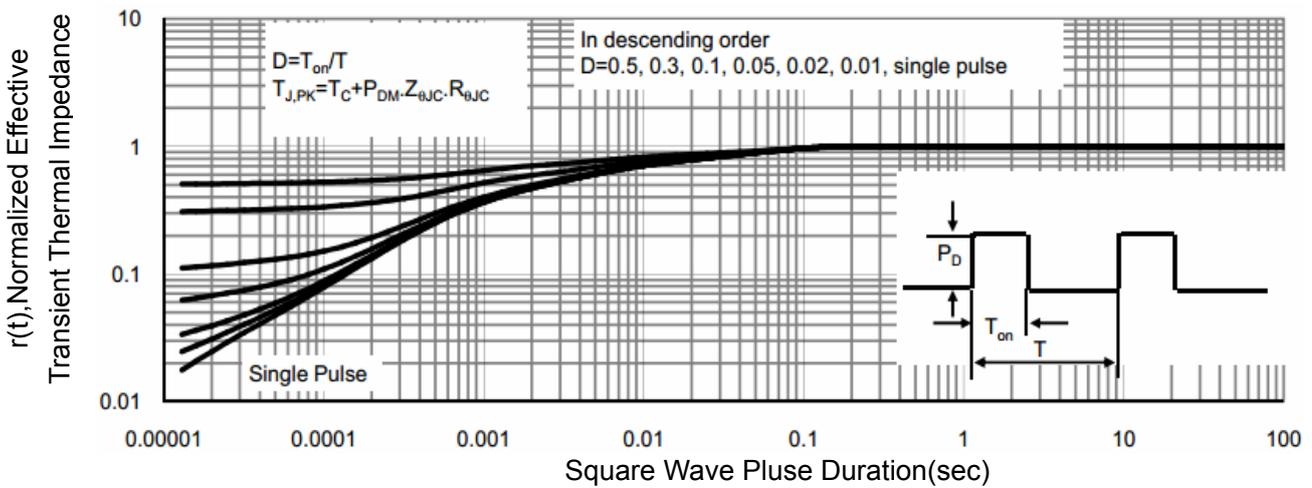
**Figure 9 Power De-rating**



**Figure 8 Safe Operation Area**

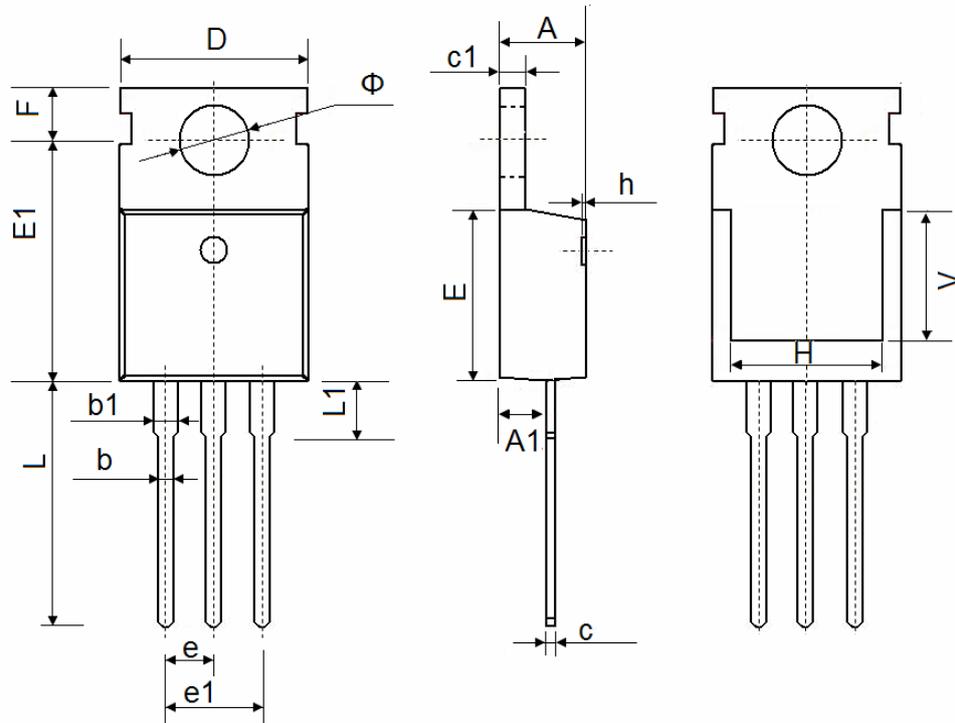


**Figure 10 Current De-rating**



**Figure 11 Normalized Maximum Transient Thermal Impedance**

## TO-220-3L Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	4.400	4.600	0.173	0.181
A1	2.250	2.550	0.089	0.100
b	0.710	0.910	0.028	0.036
b1	1.170	1.370	0.046	0.054
c	0.330	0.650	0.013	0.026
c1	1.200	1.400	0.047	0.055
D	9.910	10.250	0.390	0.404
E	8.9500	9.750	0.352	0.384
E1	12.650	12.950	0.498	0.510
e	2.540 TYP.		0.100 TYP.	
e1	4.980	5.180	0.196	0.204
F	2.650	2.950	0.104	0.116
H	7.900	8.100	0.311	0.319
h	0.000	0.300	0.000	0.012
L	12.900	13.400	0.508	0.528
L1	2.850	3.250	0.112	0.128
V	7.500 REF.		0.295 REF.	
Φ	3.400	3.800	0.134	0.150

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